10/565760 IAP6 Rec'd PCT/PTO 24 JAN 2006 PATENT APPLICATION

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Makoto IIDA

Application No.: National Stage Patent Application of PCT/JP2004/007619

Filed: January 24, 2006 Docket No.: 126790

For: A METHOD FOR PRODUCING A SINGLE CRYSTAL AND AN APPARATUS FOR

PRODUCING A SINGLE CRYSTAL

## **INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 2. Relevance of one or more non-English language reference is discussed in the present specification. See References 3-4. (Please note that Reference 3 corresponds to JP 2003-135085, cited in the specification.)
- 3. One or more reference cited herein was cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information. See References 1-2.
- 4. An English language Abstract of one or more non-English language reference is attached hereto. See References 2-3.
- 5. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and is attached, but has not been reviewed for accuracy. See References 2-3.

Respectfully submitted,

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WPB:JOC/yxm Date: January 24, 2006

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Form PTO-1449 (REV. 1/06) INFORMA		US Dept. of Commerce PATENT & TRADEMARK OFFICE TION DISCLOSURE STATEMENT		ATTY DOCKET NO. 126790			APPLICATION NO. National Stage Patent Application of PCT/JP2004/007619		
(Use several sheets if necessary)				APPLICANT Makoto IIDA					
				FILING DATE January 24, 2006					
U.S. PATENT DOCUMENTS									
Examiner Initials	Cite No.	Document Number	Da	te	Name				
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FOREIGN PATENT DOCUMENTS									
Examiner Initials	Cite No.	Document Number	Da		Country		With English Abstract	With English Translation	
	1	WO 02/00970 A1	01/03/20	02	WIPO		х		
	2	JP 2002-137987 A	05/14/20	02	JAPAN		х	Х	
	3	JP 2004-338979 A	12/02/20	04	JAPAN		х	Х	
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OTHER DOCUMENTS									
Examiner Initials	Cite (Including Author, Title, Date, Pertinent Pages, etc.) No.								
	4	V.V. VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon," Journal of Crystal Growth, 59 (1982), pp. 625-643							
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